



rf-Magnetron sputtering deposition system

- Keywords** Thin film growth, magnetron sputtering, epitaxy, heterostructures, oxides, ferroelectrics, superconductivity.
- Function** The following facility allows the epitaxial growth of oxide thin films and heterostructures.
- Present use** At present this instrument is used to prepare epitaxial ferroelectric $\text{PbZr}_x\text{Ti}_{1-x}\text{O}_3$, and superconducting $\text{YBa}_2\text{Cu}_3\text{O}_7$ thin films and heterostructures.
- Specifications**
- base pressure: 10^{-7} Torr
 - rf-power up to 300 W
 - substrate temperature up to 800°C
 - rotating sample holder for the deposition of large areas
 - off-axis rf-sputtering



Contact

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